2N2219, 2N2219A, 2N2219AL

Small Signal Switching Transistor

NPN Silicon

Features

- MIL-PRF-19500/251 Qualified
- Available as JAN, JANTX, and JANTXV

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Value	Unit
Collector - Emitter Voltage	V _{CEO}	50	Vdc
Collector - Base Voltage	V _{CBO}	75	Vdc
Emitter - Base Voltage	V _{EBO}	6.0	Vdc
Collector Current - Continuous	I _C	800	mAdc
Total Power Dissipation @ T _A = 25°C	P _T	8.0	W
Total Power Dissipation @ T _C = 25°C	P _T	3.0	W
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +200	°C

THERMAL CHARACTERISTICS

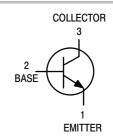
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{ heta JC}$	50	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



ON Semiconductor®

http://onsemi.com





TO-39 CASE 205AB (2N2219, 2N2219A)



TO-5 CASE 205AA (2N2219AL)

ORDERING INFORMATION

OTIDETHING INTO OTHER PROPERTY.				
Device	Package	Shipping		
JAN2N2219/A				
JANTX2N2219/A	TO-39	Bulk		
JANTXV2N2219/A				
JAN2N2219AL				
JANTX2N2219AL	TO-5	Bulk		
JANTXV2N2219AL				

2N2219, 2N2219A, 2N2219AL

ELECTRICAL CHARACTERISTICS ($T_A = 25$ °C unless otherwise noted)

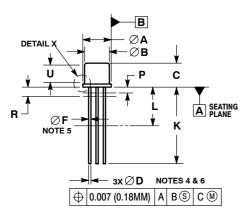
Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (I _E = 10 mAdc)	2N2219 2N2219A/AL	V _{(BR)CEO}	30 50	- -	Vdc
Emitter-Base Cutoff Current $(V_{EB} = 5.0 \text{ Vdc})$ $(V_{EB} = 6.0 \text{ Vdc})$ $(V_{EB} = 4.0 \text{ Vdc})$	2N2219 2N2219A/AL All	I _{EBO}	- - -	10 10 10	μAdc μAdc nAdc
Collector–Emitter Cutoff Current (V _{CE} = 30 Vdc) (V _{CE} = 50 Vdc)	2N2219 2N2219A/AL	I _{CES}	- -	10 10	nAdc nAdc
Collector-Base Cutoff Current (V _{CB} = 50 Vdc) (V _{CB} = 60 Vdc) (V _{CB} = 60 Vdc) (V _{CB} = 75 Vdc) ON CHARACTERISTICS (Note 1)	2N2219 2N2219 2N2219A/AL 2N2219A/AL	I _{CBO}	- - -	10 10 10 10	nAdc μAdc nAdc μAdc
DC Current Gain		h _{FE}			_
$(I_C = 0.1 \text{ mAdc}, V_{CE} = 10 \text{ Vdc})$ $(I_C = 1.0 \text{ mAdc}, V_{CE} = 10 \text{ Vdc})$	2N2219 2N2219A/AL 2N2219 2N2219A/AL		35 50 50 75	- 325 325	
$(I_C = 10 \text{ mAdc}, V_{CE} = 10 \text{ Vdc})$ $(I_C = 150 \text{ mAdc}, V_{CE} = 10 \text{ Vdc})$	2N2219 2N2219A/AL 2N2219/A/AL		75 100 100	- 300	
($I_C = 500 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$)	2N2219/A/AL		30	_) / d -
Collector – Emitter Saturation Voltage ($I_C = 150 \text{ mAdc}$, $I_B = 15 \text{ mAdc}$) ($I_C = 500 \text{ mAdc}$, $I_B = 50 \text{ mAdc}$)	2N2219 2N2219A/AL 2N2219	V _{CE(sat)}	- - -	0.4 0.3 1.6	Vdc
,	2N2219A/AL		-	1.0	
Base – Emitter Saturation Voltage $(I_C = 150 \text{ mAdc}, I_B = 15 \text{ mAdc})$	2N2219 2N2219A/AL	$V_{BE(sat)}$	0.6 0.6	1.3 1.2	Vdc
$(I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc})$	2N2219 2N2219A/AL		- -	2.6 2.0	
SMALL-SIGNAL CHARACTERISTICS					
Magnitude of Small–Signal Current Gain ($I_C = 20 \text{ mAdc}$, $V_{CE} = 20 \text{ Vdc}$, $f = 100 \text{ MHz}$)		h _{fe}	2.5	12	_
Small–Signal Current Gain ($I_C = 1.0 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1 \text{ kHz}$)	2N2219 2N2219A/AL	h _{fe}	50 75	- -	_
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, 100 kHz \leq f \leq 1.0 MHz)		C_{obo}	_	8.0	pF
Input Capacitance (V _{EB} = 0.5 Vdc, I_C = 0, 100 kHz \leq f \leq 1.0 MHz)		C _{ibo}	_	25	pF
SWITCHING CHARACTERISTICS			_	_	
Turn-On Time (Reference Figure in MIL-PRF-19500/251)	2N2219 2N2219A/AL	t _{on}	- -	40 35	ns
Turn-Off Time (Reference Figure in MIL-PRF-19500/251)	2N2219 2N2219A/AL	t _{off}	- -	250 300	ns

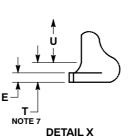
^{1.} Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%.

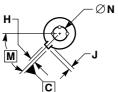
2N2219, 2N2219A, 2N2219AL

PACKAGE DIMENSIONS

TO-5 3-Lead CASE 205AA **ISSUE B**









- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: INCHES.
 3. DIMENSION J MEASURED FROM DIAMETER A TO EDGE.
 4. LEAD TRUE POSITION TO BE DETERMINED AT THE GUAGE PLANE DEFINED BY DIMENSION R.
 5. DIMENSION F. APPLIES BETWEEN DIMENSION P AND L.
 6. DIMENSION TAPPLIES BETWEEN DIMENSION LAND K.
 7. BODDY CONTOUR OPTIONAL WITHIN ZONE DEFINED BY DIMENSIONS A. B. AND T.

- SIONS A, B, AND T.

 8. DIMENSION B SHALL NOT VARY MORE THAN 0.010 IN ZONE P.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	8.89	9.40	0.350	0.370
В	8.00	8.51	0.315	0.335
С	6.10	6.60	0.240	0.260
D	0.41	0.53	0.016	0.021
E	0.23	3.18	0.009	0.125
F	0.41	0.48	0.016	0.019
Н	0.71	0.86	0.028	0.034
J	0.73	1.02	0.029	0.040
K	38.10	44.45	1.500	1.750
L	6.35		0.250	
M	45°BSC		45°	BSC
N	5.08	.08 BSC 0.200 BSC		BSC
P		1.27		0.050
R	1.37 BSC		0.054	BSC
T		0.76		0.030
U	2.54		0.100	

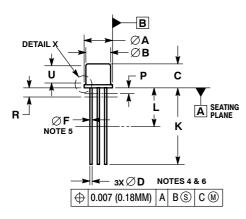
STYLE 1:

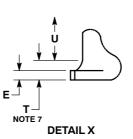
- PIN 1. EMITTER
 - BASE
 - COLLECTOR

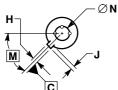
2N2219, 2N2219A, 2N2219AL

PACKAGE DIMENSIONS

TO-39 3-Lead CASE 205AB **ISSUE A**









LEAD IDENTIFICATION

DETAIL

NOTES

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. CONTROLLING DIMENSION: INCHES.
- DIMENSION J MEASURED FROM DIAMETER A TO EDGE.
- LEAD TRUE POSITION TO BE DETERMINED AT THE GUAGE PLANE DEFINED BY DIMENSION R.
- DIMENSION F APPLIES BETWEEN DIMENSION P AND L. DIMENSION D APPLIES BETWEEN DIMENSION L AND K.
- BODY CONTOUR OPTIONAL WITHIN ZONE DEFINED BY DIMENSIONS A, B, AND T.
- DIMENSION B SHALL NOT VARY MORE THAN 0.010 IN ZONE P.

	MILLIN	MILLIMETERS		HES	
DIN	1 MIN	MAX	MIN	MAX	
Α	8.89	9.40	0.350	0.370	
В	8.00	8.51	0.315	0.335	
C	6.10	6.60	0.240	0.260	
D	0.41	0.48	0.016	0.019	
E	0.23	3.18	0.009	0.125	
F	0.41	0.48	0.016	0.019	
Н	0.71	0.86	0.028	0.034	
J	0.73	1.02	0.029	0.040	
K	12.70	14.73	0.500	0.580	
L	6.35		0.250		
M	45°	45°BSC		45 °BSC	
N	5.08	5.08 BSC		0 BSC	
P		1.27		0.050	
R	1.37	1.37 BSC		BSC	
T		0.76		0.030	
U	2.54		0.100		

STYLE 1:

PIN 1. EMITTER

BASE

COLLECTOR

ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada

Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910 Japan Customer Focus Center

Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative